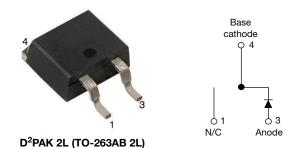
## **Vishay Semiconductors**

Hyperfast Rectifier, 30 A FRED Pt<sup>®</sup> G5



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### LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS								
I <sub>F(AV)</sub>	30 A							
V <sub>R</sub>	600 V							
V <sub>F</sub> at I <sub>F</sub> at 125 °C	1.3 V							
T <sub>J</sub> max.	175 °C							
t <sub>rr</sub> (typ.)	22 ns							
Package	D <sup>2</sup> PAK 2L (TO-263AB 2L)							
Circuit configuration	Single							

### **FEATURES**

- · Best in class forward voltage drop and switching losses trade off
- · Optimized for high speed operation
- 175 °C maximum operating junction temperature
- Polyimide passivation
- AEC-Q101 qualified, meets JESD 201 class 2 whisker test
- Meets MSL level, per J-Std-020, LF maximum peak of 245 °C
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

### **DESCRIPTION / APPLICATIONS**

Featuring a unique combination of low conduction and switching losses, this rectifier is the right choice for soft switched and resonant converters, as well as medium frequency hard switching converters. This device is specifically designed to improve efficiency of high speed LLC output rectification stages of EV / HEV battery charging stations and high frequency stages of UPS applications.

### **MECHANICAL DATA**

Case: D<sup>2</sup>PAK 2L (TO-263AB 2L)

Molding compound meets UL 94 V-0 flammability rating

Terminals: matte tin plated leads, solderable per J-STD-002

ABSOLUTE MAXIMUM RATINGS										
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS						
Repetitive peak reverse voltage	V <sub>RRM</sub>		600	V						
Average rectified forward current	I <sub>F(AV)</sub>	T <sub>C</sub> = 106 °C, D = 0.50	30							
Non-repetitive peak surge current	I <sub>FSM</sub>	$T_C = 25$ °C, $t_p = 10$ ms, sine wave	310	A						
Repetitive peak forward current	I <sub>FRM</sub>	T <sub>C</sub> = 106 °C, D = 0.50, f = 20 kHz	60							
Operating junction and storage temperature	T <sub>J</sub> , T <sub>Stg</sub>		-55 to +175	°C						

<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)										
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS				
Breakdown voltage, blocking voltage	V <sub>BR</sub> , V <sub>R</sub>	I <sub>R</sub> = 100 μA	600	-	-					
	V <sub>F</sub>	I <sub>F</sub> = 30 A	-	1.6	2.1	V				
Forward voltage		I <sub>F</sub> = 30 A, T <sub>J</sub> = 125 °C	-	1.3	-					
Poweree leekage eurrent	I <sub>R</sub>	$V_{R} = V_{R}$ rated	-	-	20					
Reverse leakage current		$T_J = 125 \text{ °C}, V_R = V_R \text{ rated}$	-	-	500	μA				
Junction capacitance	CT	V <sub>R</sub> = 200 V	-	36	-	pF				
Series inductance	L <sub>S</sub>	Measured to lead 5 mm from package body	-	8	-	nH				

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# Vishay Semiconductors

<b>DYNAMIC RECOVERY CHARACTERISTICS</b> ( $T_J = 25$ °C unless otherwise specified)										
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS				
		I <sub>F</sub> = 1.0 A,dI <sub>F</sub> /dt =	100 A/µs, V <sub>R</sub> = 30 V	-	22	-				
Reverse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	39	-	ns			
		T <sub>J</sub> = 125 °C		-	50	-				
Peak recovery current		T <sub>J</sub> = 25 °C	I <sub>F</sub> = 20 A dI <sub>F</sub> /dt = 1000 A/µs	-	14	-	A			
	IRRM	T <sub>J</sub> = 125 °C	$V_{\rm R} = 400 \text{ V}$	-	24	-				
Davience in a construction of a mark	Q <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	253	-	nC			
Reverse recovery charge		T <sub>J</sub> = 125 °C		-	785	-				
Reverse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	41	-	ns			
neverse recovery time		T <sub>J</sub> = 125 °C		-	56	-				
Peak recovery current	1	T <sub>J</sub> = 25 °C	I <sub>F</sub> = 30 A dI <sub>F</sub> /dt = 1000 A/µs	-	16	-	A			
reak recovery current	I <sub>RRM</sub>	T <sub>J</sub> = 125 °C	$V_{\rm R} = 400  \text{V}$	-	27	-				
Deverse we are a strained	0	T <sub>J</sub> = 25 °C	]	-	306	-				
Reverse recovery charge	Q <sub>rr</sub>	T <sub>J</sub> = 125 °C		-	952	-	nc			

THERMAL - MECHANICAL SPECIFICATIONS											
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS					
Thermal resistance, junction-to-case	R <sub>thJC</sub>		-	-	1.3	°C/W					
			-	2.0	-	g					
Weight			-	0.07	-	oz.					
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-55	-	175	°C					
Marking device		Case style: D <sup>2</sup> PAK 2L (TO-263AB 2L)	E5TX3006SH								



## **VS-E5TX3006S2LHM3**

## **Vishay Semiconductors**

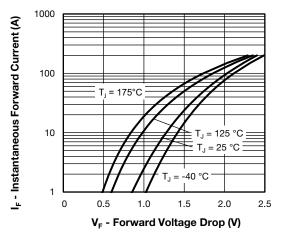


Fig. 1 - Typical Forward Voltage Drop Characteristics

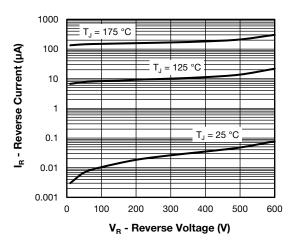


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

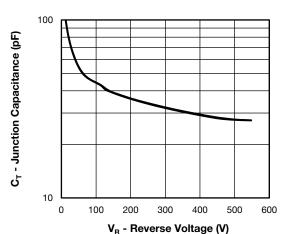
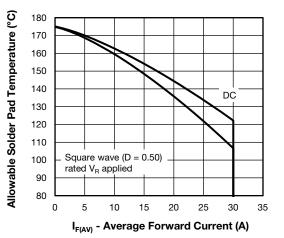
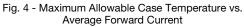


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage





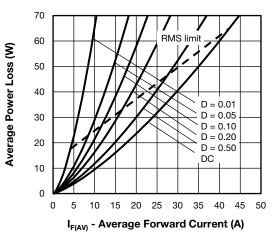


Fig. 5 - Average Power Loss vs. Average Forward Current

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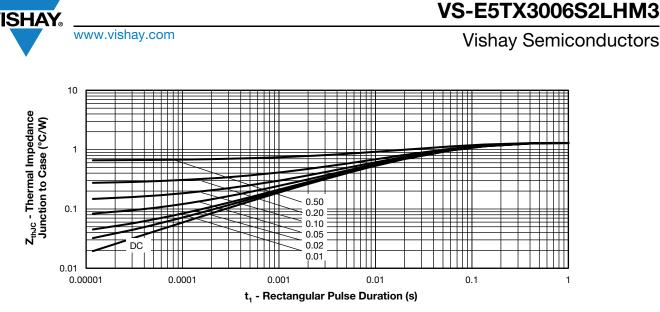


Fig. 6 - Thermal Impedance ZthJC - Characteristics

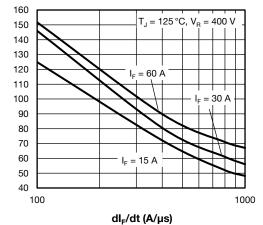


Fig. 7 - Typical Reverse Recovery Time vs. dI<sub>F</sub>/dt

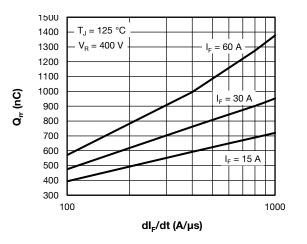


Fig. 8 - Typical Reverse Recovery Charge vs. dl<sub>F</sub>/dt

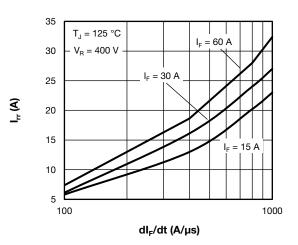


Fig. 9 - Typical Reverse Recovery Current vs. dl<sub>F</sub>/dt

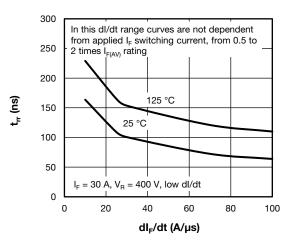


Fig. 10 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt

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# VS-E5TX3006S2LHM3

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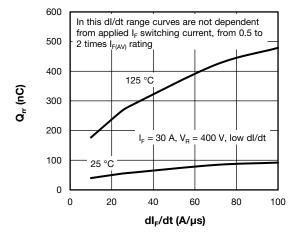


Fig. 11 - Typical Reverse Recovery Charge vs. dl<sub>F</sub>/dt

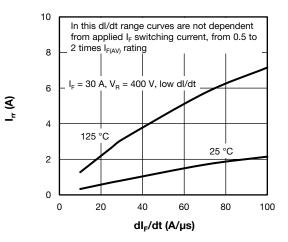


Fig. 12 - Typical Reverse Recovery Current vs. dl<sub>F</sub>/dt

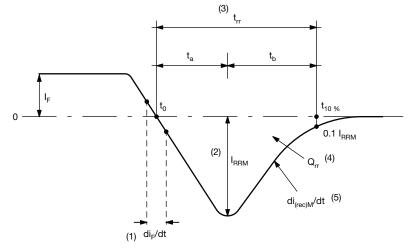


Fig. 13 - Reverse Recovery Waveform and Definitions

#### Notes

- $^{(1)}$  di<sub>F</sub>/dt rate of change of current through zero crossing
- <sup>(2)</sup> I<sub>RRM</sub> peak reverse recovery current
- $^{(3)}$  t<sub>rr</sub> reverse recovery time measured from t<sub>0</sub>, crossing point of negative going I<sub>F</sub>, to point t<sub>10%</sub>, 0.1 I<sub>RRM</sub>
- $^{(4)}~~Q_{rr}$  area under curve defined by  $t_0$  and  $t_{10}~\%$

$$Q_{rr} = \int_{t_r}^{t_{10}\%} I(t)dt$$

 $^{(5)}$  di<sub>(rec)</sub>M/dt - peak rate of change of current during t<sub>b</sub> portion of t<sub>rr</sub>

## Vishay Semiconductors



Device code	VS-	Е	5	т	x	30	06	S2	L	н	М3
	1	2	3	4	5	6	7	8	9	10	(11)
	<ul> <li>Vishay Semiconductors product</li> <li>E = single diode</li> </ul>										
	<ul> <li>3 - 5 = FRED generation 5</li> <li>4 - Package: T = D<sup>2</sup>PAK (TO-262) package</li> </ul>										
	6	- Current rating (30 = 30 A)									
	<ul> <li>7 - Voltage rating (06 = 600 V)</li> <li>8 - S2 = true 2 pin D<sup>2</sup>PAK</li> </ul>										
	<ul> <li>9 - None = tube (50 pieces)</li> <li>• L = tape and reel (left oriented, for D<sup>2</sup>PAK package) If needed different orientation/packaging, please contact factory</li> <li>10 - H = AEC-Q101 qualified</li> </ul>										
				ntal digit jen-free,		complia	ant, and	termina	ation lea	d (Pb)-f	ree

ORDERING INFORMATION (Example)							
BASE QUANTITY	PACKAGING DESCRIPTION						
800	13" diameter reel						
	BASE QUANTITY						

LINKS TO RELATED DOCUMENTS							
Dimensions	www.vishay.com/doc?96683						
Part marking information	www.vishay.com/doc?96693						
Packaging information	www.vishay.com/doc?95032						
SPICE model	www.vishay.com/doc?96918						

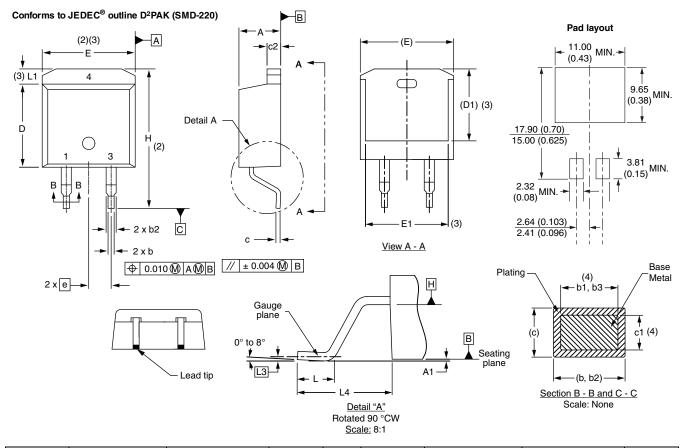
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D<sup>2</sup>PAK 2L (TO-263AB 2L)

### **DIMENSIONS** in millimeters and inches



SYMBOL	MILLIMETERS		INCHES		NOTES	, NOTES		SYMBOL	MILLIM	IETERS	INC	HES	NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES	NOTES	STWDUL	MIN.	MAX.	MIN.	MAX.	NOTES	
А	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3	
A1	0.00	0.254	0.000	0.010			Е	9.65	10.67	0.380	0.420	2, 3	
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3	
b1	0.51	0.89	0.020	0.035	4		е	2.54 BSC		0.100 BSC			
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625		
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110		
с	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3	
c1	0.38	0.58	0.015	0.023	4	L3 0.25 BSC 0.010 BSC		0.25 BSC		BSC			
c2	1.14	1.65	0.045	0.065			L4	4.78	5.28	0.188	0.208		
D	8.51	9.65	0.335	0.380	2								

#### Notes

<sup>(1)</sup> Dimensioning and tolerancing per ASME Y14.5 M-1994

(2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
 (3) Thermal and contain antional within dimension E 1.1, D1 and E1.

<sup>(3)</sup> Thermal pad contour optional within dimension E, L1, D1 and E1

<sup>(4)</sup> Dimension b1 and c1 apply to base metal only

<sup>(5)</sup> Datum A and B to be determined at datum plane H

<sup>(6)</sup> Controlling dimension: inch

(7) Outline conforms to JEDEC® outline TO-263AB

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